

DATA SHEET

74LVC2G32 Dual 2-input OR gate

Product specification
Supersedes data of 2003 Oct 27

2004 Sep 22

Dual 2-input OR gate

74LVC2G32

FEATURES

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant outputs in the Power-down mode
- High noise immunity
- Complies with JEDEC standard:
 - JESD8-7 (1.65 V to 1.95 V)
 - JESD8-5 (2.3 V to 2.7 V)
 - JESD8B/JESD36 (2.7 V to 3.6 V).
- ± 24 mA output drive ($V_{CC} = 3.0$ V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options
- ESD protection:
 - HBM EIA/JESD22-A114-B exceeds 2000 V
 - MM EIA/JESD22-A115-A exceeds 200 V.
- Specified from -40 °C to $+85$ °C and -40 °C to $+125$ °C.

DESCRIPTION

The 74LVC2G32 is a high-performance, low-power, low-voltage, Si-gate CMOS device and superior to most advanced CMOS compatible TTL families.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{off} . The I_{off} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The 74LVC2G32 provides the 2-input OR gate.

QUICK REFERENCE DATA

GND = 0 V; $T_{amb} = 25$ °C; $t_r = t_f \leq 2.5$ ns.

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t_{PHL}/t_{PLH}	propagation delay inputs nA, nB to output nY	$V_{CC} = 1.8$ V; $C_L = 30$ pF; $R_L = 1$ k Ω	3.9	ns
		$V_{CC} = 2.5$ V; $C_L = 30$ pF; $R_L = 500$ Ω	2.4	ns
		$V_{CC} = 2.7$ V; $C_L = 50$ pF; $R_L = 500$ Ω	2.7	ns
		$V_{CC} = 3.3$ V; $C_L = 50$ pF; $R_L = 500$ Ω	2.2	ns
		$V_{CC} = 5.0$ V; $C_L = 50$ pF; $R_L = 500$ Ω	1.7	ns
C_I	input capacitance		2.5	pF
C_{PD}	power dissipation capacitance per gate	$V_{CC} = 3.3$ V; notes 1 and 2	14	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts;

N = total load switching outputs;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

2. The condition is $V_i = \text{GND to } V_{CC}$.

Dual 2-input OR gate

74LVC2G32

FUNCTION TABLE

See note 1.

INPUT		OUTPUT
nA	nB	nY
L	L	L
L	H	H
H	L	H
H	H	H

Note

1. H = HIGH voltage level;
L = LOW voltage level.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE					
	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE	MARKING
74LVC2G32DP	−40 °C to +125 °C	8	TSSOP8	plastic	SOT505-2	V32
74LVC2G32DC	−40 °C to +125 °C	8	VSSOP8	plastic	SOT765-1	V32
74LVC2G32GM	−40 °C to +125 °C	8	XSON8	plastic	SOT833-1	V32

PINNING

PIN	SYMBOL	DESCRIPTION
1	1A	data input 1A
2	1B	data input 1B
3	2Y	data output 2Y
4	GND	ground (0 V)
5	2A	data input 2A
6	2B	data input 2B
7	1Y	data output 1Y
8	V _{CC}	supply voltage

Dual 2-input OR gate

74LVC2G32

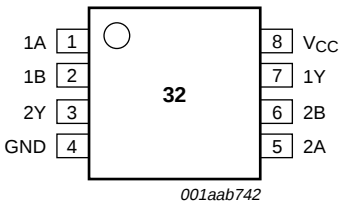


Fig.1 Pin configuration TSSOP8 and VSSOP8.

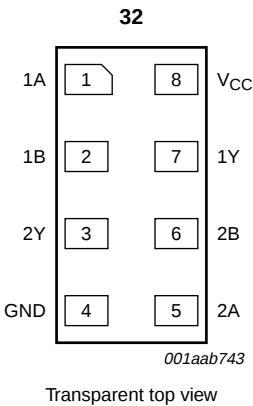


Fig.2 Pin configuration XSON8.

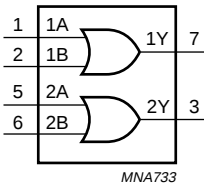


Fig.3 Logic symbol.

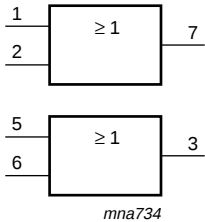
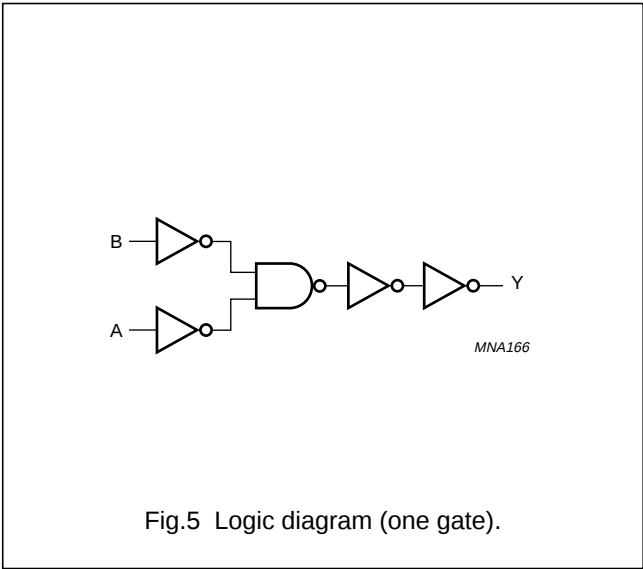


Fig.4 IEC logic symbol.

Dual 2-input OR gate

74LVC2G32



RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	supply voltage		1.65	5.5	V
V _I	input voltage		0	5.5	V
V _O	output voltage	active mode	0	V _{CC}	V
		V _{CC} = 0 V; Power-down mode	0	5.5	V
T _{amb}	ambient temperature		−40	+125	°C
t _r , t _f	input rise and fall times	V _{CC} = 1.65 V to 2.7 V	0	20	ns/V
		V _{CC} = 2.7 V to 5.5 V	0	10	ns/V

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	supply voltage		−0.5	+6.5	V
I _{IK}	input diode current	V _I < 0 V	−	−50	mA
V _I	input voltage	note 1	−0.5	+6.5	V
I _{OK}	output diode current	V _O > V _{CC} or V _O < 0 V	−	±50	mA
V _O	output voltage	active mode; notes 1 and 2	−0.5	V _{CC} + 0.5	V
		Power-down mode; notes 1 and 2	−0.5	+6.5	V
I _O	output source or sink current	V _O = 0 V to V _{CC}	−	±50	mA
I _{CC} , I _{GND}	V _{CC} or GND current		−	±100	mA
T _{stg}	storage temperature		−65	+150	°C
P _D	power dissipation per package	T _{amb} = −40 °C to +125 °C	−	300	mW

Notes

1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. When V_{CC} = 0 V (Power-down mode), the output voltage can be 5.5 V in normal operation.

Dual 2-input OR gate

74LVC2G32

DC CHARACTERISTICS

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	TEST CONDITIONS		MIN.	TYP. ⁽¹⁾	MAX.	UNIT
		OTHER	V _{CC} (V)				
T _{amb} = −40 °C to +85 °C							
V _{IH}	HIGH-level input voltage		1.65 to 1.95	0.65 × V _{CC}	–	–	V
			2.3 to 2.7	1.7	–	–	V
			2.7 to 3.6	2.0	–	–	V
			4.5 to 5.5	0.7 × V _{CC}	–	–	V
V _{IL}	LOW-level input voltage		1.65 to 1.95	–	–	0.35 × V _{CC}	V
			2.3 to 2.7	–	–	0.7	V
			2.7 to 3.6	–	–	0.8	V
			4.5 to 5.5	–	–	0.3 × V _{CC}	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}					
		I _O = −100 μA	1.65 to 5.5	V _{CC} − 0.1	–	–	V
		I _O = −4 mA	1.65	1.2	1.53	–	V
		I _O = −8 mA	2.3	1.9	2.13	–	V
		I _O = −12 mA	2.7	2.2	2.50	–	V
		I _O = −24 mA	3.0	2.3	2.60	–	V
I _O = −32 mA	4.5	3.8	4.10	–	V		
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}					
		I _O = 100 μA	1.65 to 5.5	–	–	0.1	V
		I _O = 4 mA	1.65	–	0.08	0.45	V
		I _O = 8 mA	2.3	–	0.14	0.3	V
		I _O = 12 mA	2.7	–	0.19	0.4	V
		I _O = 24 mA	3.0	–	0.37	0.55	V
I _O = 32 mA	4.5	–	0.43	0.55	V		
I _{LI}	input leakage current	V _I = 5.5 V or GND	5.5	–	±0.1	±5	μA
I _{off}	power OFF leakage current	V _I or V _O = 5.5 V	0	–	±0.1	±10	μA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0 A	5.5	–	0.1	10	μA
ΔI _{CC}	additional quiescent supply current per pin	V _I = V _{CC} − 0.6 V; I _O = 0 A	2.3 to 5.5	–	5	500	μA

Dual 2-input OR gate

74LVC2G32

SYMBOL	PARAMETER	TEST CONDITIONS		MIN.	TYP. ⁽¹⁾	MAX.	UNIT
		OTHER	V _{CC} (V)				
T _{amb} = −40 °C to +125 °C							
V _{IH}	HIGH-level input voltage		1.65 to 1.95	0.65 × V _{CC}	–	–	V
			2.3 to 2.7	1.7	–	–	V
			2.7 to 3.6	2.0	–	–	V
			4.5 to 5.5	0.7 × V _{CC}	–	–	V
V _{IL}	LOW-level input voltage		1.65 to 1.95	–	–	0.35 × V _{CC}	V
			2.3 to 2.7	–	–	0.7	V
			2.7 to 3.6	–	–	0.8	V
			4.5 to 5.5	–	–	0.3 × V _{CC}	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}					
		I _O = −100 μA	1.65 to 5.5	V _{CC} − 0.1	–	–	V
		I _O = −4 mA	1.65	0.95	–	–	V
		I _O = −8 mA	2.3	1.7	–	–	V
		I _O = −12 mA	2.7	1.9	–	–	V
		I _O = −24 mA	3.0	2.0	–	–	V
		I _O = −32 mA	4.5	3.4	–	–	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}					
		I _O = 100 μA	1.65 to 5.5	–	–	0.1	V
		I _O = 4 mA	1.65	–	–	0.70	V
		I _O = 8 mA	2.3	–	–	0.45	V
		I _O = 12 mA	2.7	–	–	0.60	V
		I _O = 24 mA	3.0	–	–	0.80	V
		I _O = 32 mA	4.5	–	–	0.80	V
I _{LI}	input leakage current	V _I = 5.5 V or GND	5.5	–	±0.1	±20	μA
I _{off}	power OFF leakage current	V _I or V _O = 5.5 V	0	–	–	±20	μA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0 A	5.5	–	–	40	μA
ΔI _{CC}	additional quiescent supply current per pin	V _I = V _{CC} − 0.6 V; I _O = 0 A	2.3 to 5.5	–	–	5000	μA

Note

1. All typical values are measured at T_{amb} = 25 °C.

Dual 2-input OR gate

74LVC2G32

AC CHARACTERISTICS

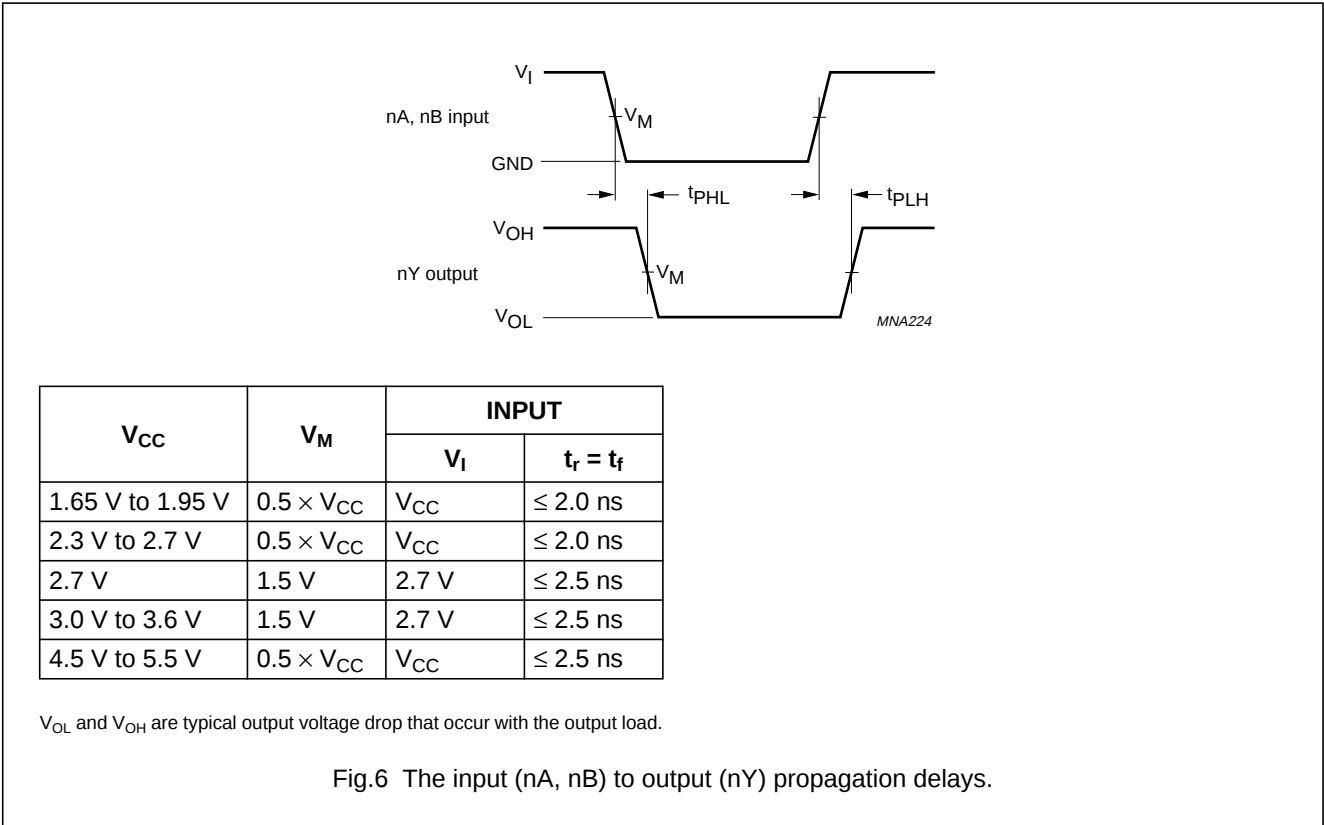
GND = 0 V.

SYMBOL	PARAMETER	TEST CONDITIONS		MIN.	TYP. ⁽¹⁾	MAX.	UNIT
		WAVEFORMS	V _{CC} (V)				
T _{amb} = −40 °C to +85 °C							
t _{PHL} /t _{PLH}	propagation delay nA, nB to nY	see Figs 6 and 7	1.65 to 1.95	1.3	3.9	8.8	ns
			2.3 to 2.7	0.8	2.4	4.7	ns
			2.7	0.8	2.7	4.8	ns
			3.0 to 3.6	0.9	2.2	4.2	ns
			4.5 to 5.5	0.7	1.7	3.2	ns
T _{amb} = −40 °C to +125 °C							
t _{PHL} /t _{PLH}	propagation delay nA, nB to nY	see Figs 6 and 7	1.65 to 1.95	1.3	—	11	ns
			2.3 to 2.7	0.8	—	5.9	ns
			2.7	0.8	—	6.0	ns
			3.0 to 3.6	0.9	—	5.3	ns
			4.5 to 5.5	0.7	—	4.0	ns

Note

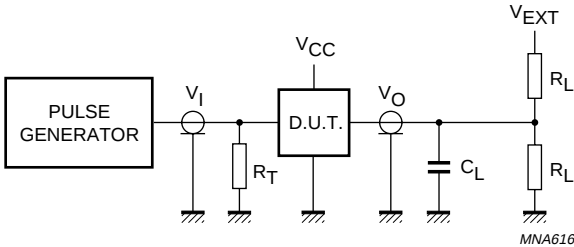
1. All typical values are measured at T_{amb} = 25 °C.

AC WAVEFORMS



Dual 2-input OR gate

74LVC2G32



V _{CC}	V _I	C _L	R _L	V _{EXT}		
				t _{PLH} /t _{PHL}	t _{PZH} /t _{PHZ}	t _{PZL} /t _{PLZ}
1.65 V to 1.95 V	V _{CC}	30 pF	1 kΩ	open	GND	2 × V _{CC}
2.3 V to 2.7 V	V _{CC}	30 pF	500 Ω	open	GND	2 × V _{CC}
2.7 V	2.7 V	50 pF	500 Ω	open	GND	6 V
3.0 V to 3.6 V	2.7 V	50 pF	500 Ω	open	GND	6 V
4.5 V to 5.5 V	V _{CC}	50 pF	500 Ω	open	GND	2 × V _{CC}

Definitions for test circuit:
R_L = Load resistor.
C_L = Load capacitance including jig and probe capacitance.
R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

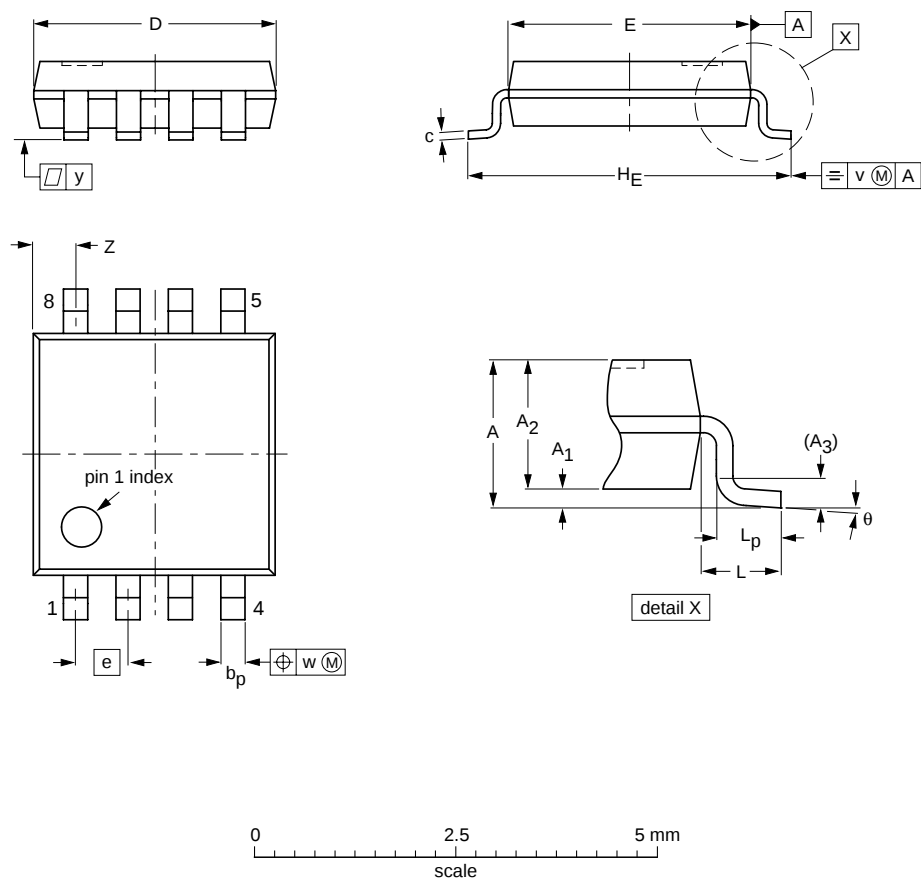
Fig.7 Load circuitry for switching times.

Dual 2-input OR gate

74LVC2G32

PACKAGE OUTLINES

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2



DIMENSIONS (mm are the original dimensions)

UNIT	A _{max.}	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	H _E	L	L _p	v	w	y	z ⁽¹⁾	θ
mm	1.1	0.15 0.00	0.95 0.75	0.25	0.38 0.22	0.18 0.08	3.1 2.9	3.1 2.9	0.65	4.1 3.9	0.5	0.47 0.33	0.2	0.13	0.1	0.70 0.35	8° 0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

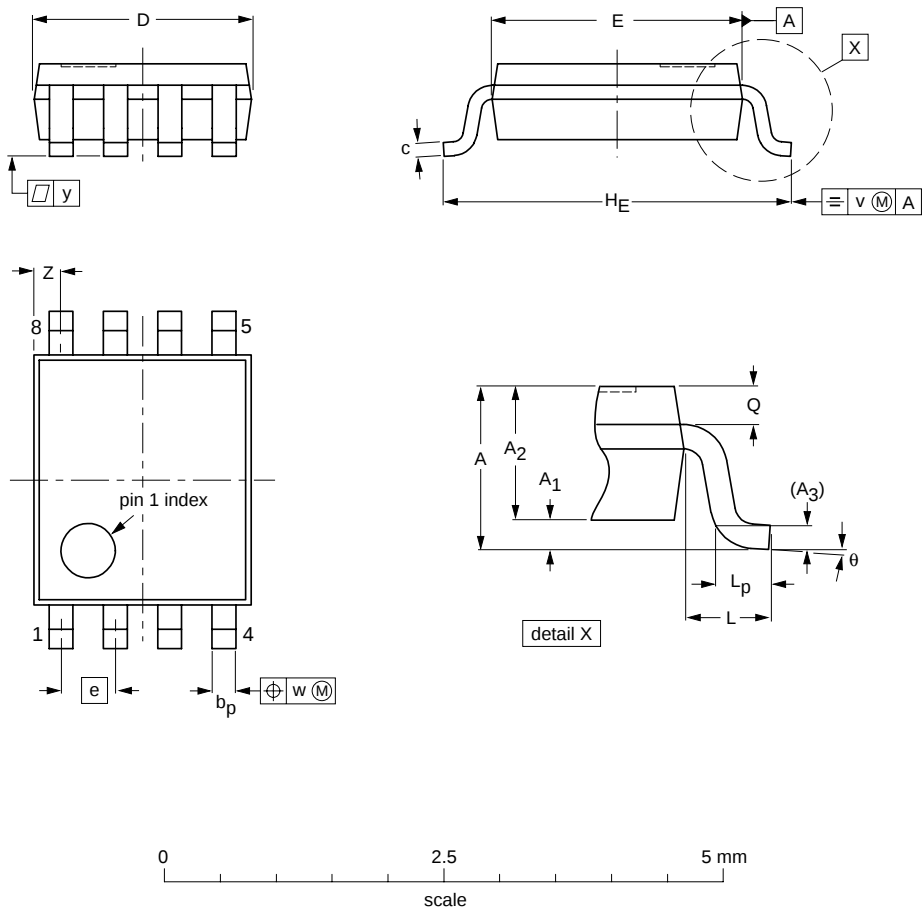
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT505-2		---				02-01-16

Dual 2-input OR gate

74LVC2G32

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽²⁾	e	H _E	L	L _p	Q	v	w	y	z ⁽¹⁾	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

- Notes
- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
 - 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

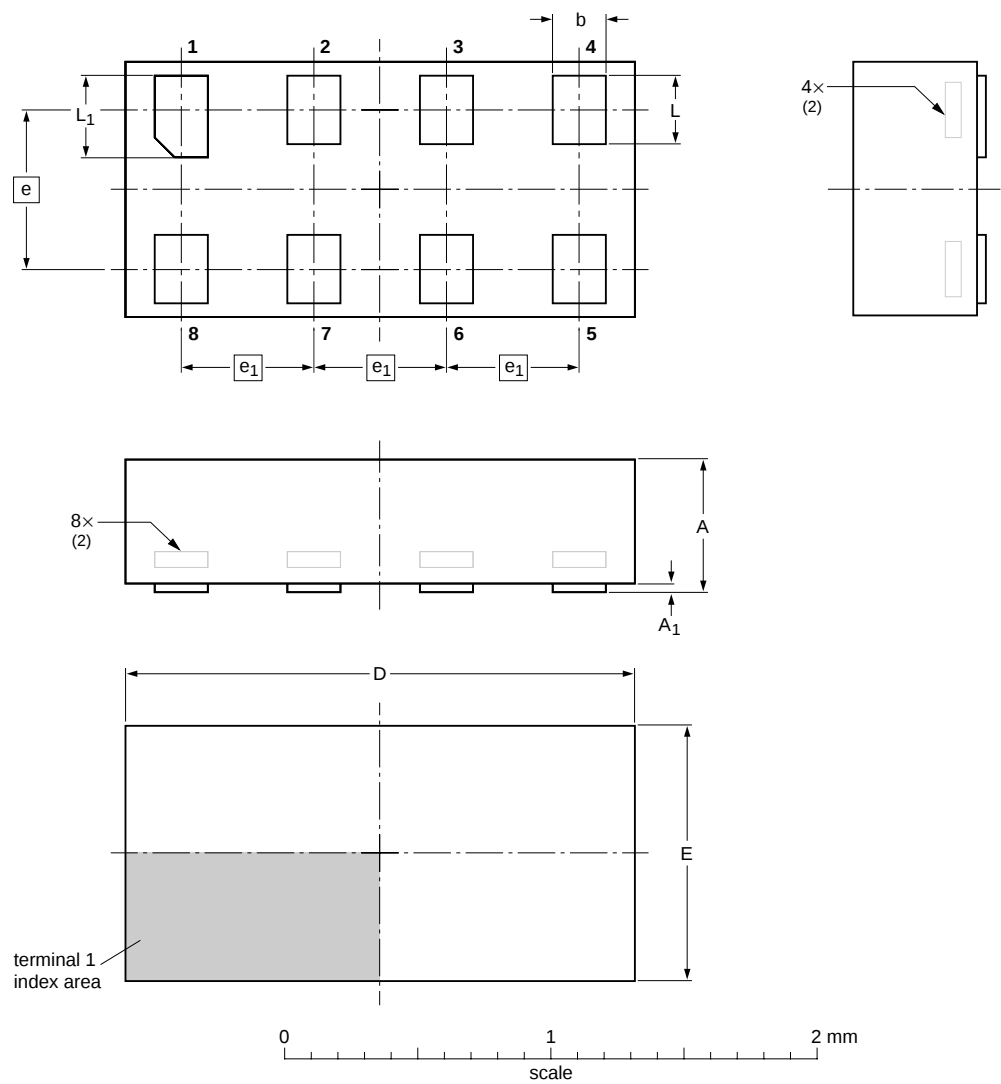
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	IEC	JEDEC	JEITA			
SOT765-1		MO-187				02-06-07

Dual 2-input OR gate

74LVC2G32

XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 0.95 x 1.95 x 0.5 mm

SOT833-1



DIMENSIONS (mm are the original dimensions)

UNIT	A ⁽¹⁾ max	A ₁ max	b	D	E	e	e ₁	L	L ₁
mm	0.5	0.04	0.25 0.17	2.0 1.9	1.0 0.9	0.6	0.5	0.35 0.27	0.40 0.32

- Notes
- 1. Including plating thickness.
 - 2. Can be visible in some manufacturing processes.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT833-1	---	MO-252	---			04-07-15 04-07-22

Dual 2-input OR gate

74LVC2G32

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
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II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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